

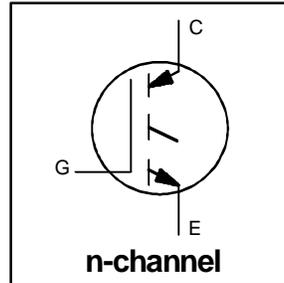
IRGPH40M

INSULATED GATE BIPOLAR TRANSISTOR

Short Circuit Rated
Fast IGBT

Features

- Short circuit rated - $10\mu\text{s}$ @ 125°C , $V_{GE} = 15\text{V}$
- Switching-loss rating includes all "tail" losses
- Optimized for medium operating frequency (1 to 10kHz)



$$V_{CES} = 1200\text{V}$$

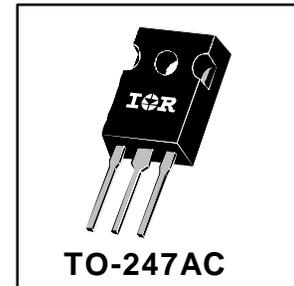
$$V_{CE(sat)} \leq 3.4\text{V}$$

$$\text{@ } V_{GE} = 15\text{V}, I_C = 18\text{A}$$

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
I_C @ $T_C = 25^\circ\text{C}$	Continuous Collector Current	31	A
I_C @ $T_C = 100^\circ\text{C}$	Continuous Collector Current	18	
I_{CM}	Pulsed Collector Current ①	62	
I_{LM}	Clamped Inductive Load Current ②	62	
t_{sc}	Short Circuit Withstand Time	10	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	15	mJ
P_D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	160	W
P_D @ $T_C = 100^\circ\text{C}$	Maximum Power Dissipation	65	
T_J	Operating Junction and	-55 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.77	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ③	20	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.1	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.3	3.4	V	$I_C = 18A$ $I_C = 31A$ $I_C = 18A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$
		—	3.0	—		
		—	2.8	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-14	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ④	4.0	10	—	S	$V_{CE} = 100V, I_C = 18A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 1200V$
		—	—	3500		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	50	75	nC	$I_C = 18A$	
Q_{ge}	Gate - Emitter Charge (turn-on)	—	11	21		$V_{CC} = 400V$	
Q_{gc}	Gate - Collector Charge (turn-on)	—	15	30		$V_{GE} = 15V$	
$t_{d(on)}$	Turn-On Delay Time	—	30	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 18A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 10\Omega$ Energy losses include "tail"	
t_r	Rise Time	—	21	—			
$t_{d(off)}$	Turn-Off Delay Time	—	400	890			
t_f	Fall Time	—	390	740			
E_{on}	Turn-On Switching Loss	—	1.1	—			mJ
E_{off}	Turn-Off Switching Loss	—	6.3	—			
E_{ts}	Total Switching Loss	—	7.4	14			
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 720V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 10\Omega, V_{CPK} < 1000V$	
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 18A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 10\Omega$ Energy losses include "tail"	
t_r	Rise Time	—	24	—			
$t_{d(off)}$	Turn-Off Delay Time	—	600	—			
t_f	Fall Time	—	870	—			
E_{ts}	Total Switching Loss	—	15	—			mJ
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	1360	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$	
C_{oes}	Output Capacitance	—	100	—			
C_{res}	Reverse Transfer Capacitance	—	15	—			

Notes:

- ① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature. ③ Repetitive rating; pulse width limited by maximum junction temperature. ⑤ Pulse width 5.0 μs , single shot.
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=10\Omega$ ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.

Refer to Section D - page D-13 for Package Outline 3 - JEDEC Outline TO-247AC